



Bipolar NPN Bare Die – BTN6048

Part Description

The BTN6048 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 250V
- VCEO = 200V
- VEBO = 6V
- hFE = 40-160 @ VCE = 5V, IC = 0.5A
- VCE(Sat) = 0.2V @ IC = 0.5A, IB = 50mA
- fT = 50 MHz @ VCE = 10V, IE = 0A
- COBO = 30pF @ VCB = 10V

Features

Low VCE(sat). Designed to provide performance equivalent to BUY49

Die Size (Unawn)

1300 μ m X 1300 μ m, 51 Mils X 51 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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